

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	09/945535
	Filing Date	August 30, 2001
	First Named Inventor	Ahn, Kie
	Group Art Unit	2813
	Examiner Name	Blum, David
Sheet 1 of 1		Attorney Docket No: 1303.026US1

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
12/17	US-2001/0009695	07/26/2001	Saaniia, Ville A., et al.	427	255.39	01/18/2001
	US-2002/0146916	10/10/2002	Irino, Kiyoshi, et al.	438	785	03/29/2002
	US-2003/0175411	09/18/2003	Kodas, T. T., et al.	427	58	10/04/2002
	US-6,093,944	07/25/2003	VanDover, R B.	257	310	06/04/1998
	US-6,451,695	09/17/2002	Sneh, O.	438	685	12/22/2000
	US-6,602,338	08/05/2003	Chen, S., et al.	106	287.19	04/11/2001

FOREIGN PATENT DOCUMENTS						
Examiner Initials *	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
12/17		CHAMBERS, J J., et al., "Physical and electrical characterization of ultrathin yttrium silicate insulators on silicon", <u>Journal of Applied Physics</u> , 90(2), (July 15, 2001), 918-33	
		KUKLI, KAUPPO, et al., "Low-Temperature Deposition of Zirconium Oxide-Based Nanocrystalline Films by Alternate Supply of Zr[OC(CH ₃) ₃] ₄ and H ₂ O", <u>Chemical Vapor Deposition</u> , 6(6), (2000), 297-302	
		NAKAJIMA, ANRI, "Soft breakdown free atomic-layer-deposited silicon-nitride/SiO ₂ /sub 2/ stack gate dielectrics", <u>International Electron Devices Meeting. Technical Digest</u> , (2001), 6.5.1-4	
		RAHTU, ANTTI, et al., "Atomic Layer Deposition of Zirconium Titanium Oxide from Titanium Isopropoxide and Zirconium Chloride", <u>Chemistry of Materials</u> , 13(5), (May 2001), 1528-1532	
		WOLF, S., et al., In: <u>Silicon Processing of the VLSI Era, Vol. 1</u> , Lattice Press, 374-380	

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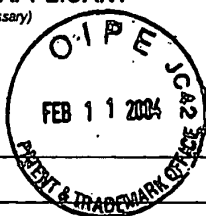
DATE CONSIDERED

4/27/04

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Substitute Disclosure Statement Form (PTO-1449)

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